Temperature Compensated Crystal Oscillator (TCXO)

- · Package size (5.0 mm × 3.2 mm × 1.45 mm)
- · Ultra high stability VC-TCXO
- · Output waveform : CMOS
- · Reference weight Typ.72 mg
- [1] Product Number / Product Name
- (1-1) Product Number / Ordering Code

X1G0053910030xx

- last 2 digits code(xx) define Quantity.
- The standard is "00", 1 000 pcs/Reel.
- (1-2) Product Name / Model Name

TG5032CFN 19.440000 MHz CBGNEA

[2] Operating range

Parameter	Symbol	0,	Specification	S	Unit	Conditions
T drameter	Symbol	Min.	Min. Typ. Max.		Onit	Conditions
Supply voltage	Vcc	3.135	3.3	3.465	V	-
Supply voltage	GND	0	-	0	V	-
Frequency control voltage	Vc	0.65	1.65	2.65	V	Vc = 1.65 ±1.0 V
Operating temperature range	T_use	-40	-	+85	°C	-
Output load	Load_C	13.5	15	16.5	pF	-

[3] Frequency characteristics

(Vcc = 3.3 V, GND = 0.0 V, Vc = 1.65 V, Load = 15 pF, T_use = +25 °C) (1) Frequency characteristics

		Specification	<u> </u>				
Parameter	Symbol				Unit	Conditions	
Output Frequency	fo	Min.	<u>Typ.</u> 19.44	Max.	MHz		
Frequency tolerance *1	f_tol	-1.0	-	+1.0	x10 ⁻⁶	T_use = +25 °C ±2 °C After 2 reflows *2	
Frequency / temperature characteristics	fo-Tc	-0.28	-	+0.28	x10⁻⁵	T_use = -40 °C to +85 °C (Reference to (fmax+fmin)/2)	
Frequency / load coefficient	fo-Load	-0.1	-	+0.1	x10⁻⁵	Load ±10 %	
Frequency / voltage coefficient	fo-Vcc	-0.1	-	+0.1	x10⁻⁵	Vcc ±5 %	
Frequency aging	f_age	-0.5	-	+0.5	x10⁻⁵	T_use = +25 °C first year	
Frequency aging		-3.0	-	+3.0	x10⁻⁵	T_use = +25 °C 20 years	
Holdover stability, constant temperature	-	-0.01	-	+0.01	x10⁻⁵	T_use = +25 °C, 24 hours (after 10 days of continuous operation)	
Holdover stability, constant temperature	-	-0.04	-	+0.04	x10⁻⁵	T_use = +25 °C, 24 hours (after 48 hours of continuous operation)	
Holdover stability (Free-run accuracy)	-	-4.6	-	+4.6	x10⁻⁵	*3	

*1 Include initial frequency tolerance and frequency deviation after reflow cycles.

*2 Measured in the elapse of 24 hours after reflow soldering.

*3 This includes initial frequency tolerance, frequency / temperature characteristics, frequency / load coefficient, frequency/voltage coefficient and frequency aging (+25 °C, 20 years) .

(2) Frequency control characteristics

(Vcc = 3.3 V, GND = 0.0 V, Vc = 1.65 V, Load = 15 pF, T_use = +25 °C)

Parameter	Svmbol	0,	Specification	S	Unit	Conditions
i alametei	Symbol	Min.	Tvp.	Max.	Unit	
Frequency control range	f cont	-10	-	-5	x10⁻⁵	Vc = 0.65 V
	1_00m	+5	-	+10	x10⁻⁵	Vc = 2.65 V
Input impedance	Zin	100	-	-	kΩ	Vc = 1.65 V
Frequency change polarity	-	Positive polarity			-	-

[4] Electrical characteristics

[4] Electrical characterist	ctrical characteristics (Vcc = 3.3 V, GND = 0.0 V					Load = 15 pF, T_use = +25 °C)
Parameter	Symbol		Specification	S	Unit	Conditions
i arameter	Symbol	Min.	Typ.	Max.	Onit	Conditions
Current consumption	lcc	-	-	5.0	mA	-
High level output voltage	Vон	90 %	-	-	V	-
Low level output voltage	Vol	-	-	10 %	V	-
Rise time	tr	-	-	8.0	ns	10 % Vcc to 90 % Vcc level
Fall time	tf	-	-	8.0	ns	90 % Vcc to 10 % Vcc level
Symmetry	SYM	45	-	55	%	50 % Vcc Level

[For other general specifications, please refer to the attached Full Data Sheet below]

Ultra high stability temperature compensated crystal oscillator <u>Product name : TG5032CFN / TG5032SFN</u>

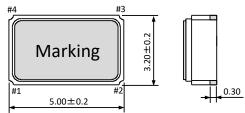
Features

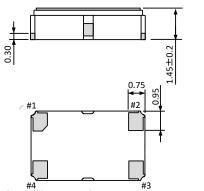
- Ultra high stability ($\leq 0.1 \times 10^{-6}$)
- Low phase noise
- Frequency range : 10 MHz to 40 MHz
- Output : CMOS, Clipped sine wave
- Supply voltage : 2.375 to 3.63 V
- External dimensions : 5.0 × 3.2 × 1.45 mm
- Small size package (4 pads)
- Pb free.
- Complies with EU RoHS directive.

Applications

- Small Cells
- Stratum3
- Femtocell
- Network system etc..

Outline dimensions





Pin information

Pin	Connections							
FIII	VC-TCXO	тсхо						
1	Vc	N.C.						
2	GNI	C						
3	OUT							
4	Vcc							



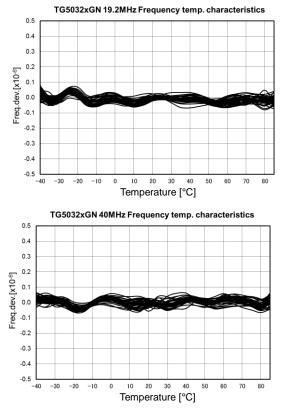
Description

This product is ultra high stability temperature compensated crystal oscillator of CMOS and Clipped sine wave outputs using fundamental oscillation of Crystal unit. This has realized a low phase noise in frequency 10 to 40 MHz, and it is suitable for the reference clock include Small Cells.

This allows the product to be compliant with various standards including GR-1244-CORE Stratum3, G.8262.1, G.8273.2 (Class A,B).

Characteristics

Frequency / temperature characteristics



1. Product Number / Product Name

(1-1) Product Number / Ordering Code

TG5032CFN: X1G005391xxxx00 (Please contact Epson for details of number xxxx)

(The last 2 digits code (00) define Quantity. 1 000 pcs/Reel) TG5032SFN: X1G005401xxxx00

(1-2) Product Name / Model Name (Standard form)

TG5032CFN 10.00000MHz CAGNDA

3 456789

2 Output

С

CMOS

① Model

1

- (2) Output
- ③ Frequency
- ④ Supply voltage
- 5 Frequency / temperature

2

6 Operation temperature

⑦ OE function (H: Non)

(8) Vc function (Non Filter)

(9) Internal identification code ("A" is default)

S	Clipped sine Wave	В	±0.28 x 10 ⁻⁶
4	Supply voltage	6	Operation te
С	33∨	G	-40 °C to +85

G	-40 °C to +85 °C

±0.1 x 10⁻⁶

А

8	Vc function	Filter option
Ν	Non Vc	
Е	Vc = 1.65 V	Non Filter
D	Vc = 1.5 V	

1	OE function
Ν	Non OE function

5 Frequency / temperature

Operation temperature

2. Electrical characteristics

1) Absolute maximum ratings

	_					
Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
Supply voltage	Vcc-GND	V	-0.5	-	+4.0	
Storage temperature	T_stg	°C	-40	-	+90	Store as bare product after packing
Frequency control voltage	Vc-GND	V	-0.5	-	Vcc+0.5	Vc Terminal

2) Operating conditions

Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
	Maa		2.375	-	3.63	Supply voltage range
Supply voltage	Vcc	V	2.85	3.0	3.15	V _{CC} = 3.0 V Type
	GND		0.0	-	0.0	
Operating temperature range	T_use	°C	-40	+25	+85	Standard
	Vc		GND	N.C.	-	Vc Terminal / TCXO
Frequency control voltage		V	0.5	1.5	2.5	V _c Terminal / VC-TCXO
			0.65	1.65	2.65	
	Load_C	pF	13.5	15	16.5	CMOS output
	Load_C	pF	9	10	11	Clipped sine wave
Output load condition	Load_R	kΩ	9	10	11	Clipped sine wave
	Сс	μF	0.01	-	-	DC-cut capacitor *1 Clipped sine wave

*1 DC-cut capacitor is not included in this TCXO. Please attach an external DC-cut capacitor (0.01 µF Min.) to the out pin.

3-1) Frequency characteristics

(V_{CC} = Typ., GND = 0.0 V, V_C = Typ. V, Load = Typ., T_use = +25 °C)

Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
			10	-	40	
Output frequency	fo	MHz			24,576, 25, 4, 38.88, 40	Standard frequency list
Frequency tolerance *2 (T_use=+25 °C ±2 °C) (Reflow cycles : 2 times)	f_tol	× 10⁻ ⁶	-1.0	-	+1.0	
Frequency / temperature			-0.10	-	+0.10	T_use = -40 °C to +85 °C (Standard)
characteristics	fo-Tc	× 10⁻ ⁶	-0.14	-	+0.14	T_use = -40 °C to +85 °C
(Reference to (fmax+fmin)/2.)	10-10	× 10	-0.25	-	+0.25	T_use = -40 °C to +85 °C
			-0.28	-	+0.28	T_use = -40 °C to +85 °C
Frequency / load coefficient	fo-Load	× 10 ⁻⁶	-0.10	-	+0.10	Load ±10 %
Frequency / load coefficient	10-LUau	x 10 ⁻¹	-0.05	-	+0.05	Load ±2%
Frequency / voltage	fo- Vcc	× 10⁻ ⁶	-0.10	-	+0.10	Vcc ±5 %
coefficient	10- VCC	× 10	-0.05	-	+0.05	Vcc ±2%
Frequency slope	-	× 10⁻ ⁶ /°C	-0.10	-	+0.10	Minimum of 1 frequency reading every 2 °C, over the operating temperature range (1 °C/minute max.)
Hysteresis	-	× 10 ⁻⁶	-0.20	-	+0.20	Frequency measured before and after at +25 °C.
Fraguanay aging *6	fore	× 10⁻ ⁶	-0.5	-	+0.5	T_use = +25 °C, First year
Frequency aging *6	f_age	× 10 °	-3.0	-	+3.0	T_use = +25 °C, 20 years
Holdover stability		× 10⁻ ⁶	-0.01	-	+0.01	T_use = +25 °C, 1 day *3
(Constant temperature)	-	× 10-	-0.04	-	+0.04	T_use = +25 °C, 1 day *4
Holdover stability (Free-run accuracy)	-	× 10 ⁻⁶	-4.6	-	+4.6	*5
Acceleration sensitivity	-	× 10 ⁻⁹ / G	-	2.0	-	3 axes, 30-1500 Hz

*2 Measured 24 hours after reflow soldering.

*3 After 10 days of continuous operation.

*4 After 48 hours of continuous operation.

*5 This includes initial frequency tolerance, frequency / temperature characteristics, frequency / load coefficient, frequency/voltage coefficient and frequency aging (+25 °C, 20 years)

*6 Aging stability is estimated from environmental reliability tests and the expected amount of the frequency variation over time. It is not intend as a guarantee of performance over the product-life cycle

3-2) Frequency cont							Vc = 1	Гур. V, Load = Тур., T_use = +25 °С)
Parameter	Symbo	ol Unit	Min.	Тур.		lax		Notes
Frequency control range	f_cont	× 10 ⁻⁶	-10.0	-		5.0	Vc =	= 1.5 V±1.0 V, Vc = 1.65 V±1.0 V
			+5.0	-	+10.0			,
Linearity Input impedance	- Zin	% kΩ	-10 100	-	+	-10	Vo-C	GND(DC), Vc = Typ.
Frequency change polarity	ZIN -	-		sitive polari	itv	-	vc-c	SND(DC), VC = Typ.
	ariation					0.01/1		
4) Electrical Charact				= Typ., GN	ID =	0.0 V,	VC =	Typ. V, Load = Typ., T_use = +25 °C)
Parameter	Symbol	Unit	Min.	Тур.		Ma		Notes
		mA	-	-		5.0		Clipped sine wave (Standard)
Current consumption	lcc		-	-		3.0		Clipped sine wave (Option)
			-	-		5.0 6.0		CMOS (~26 MHz) CMOS (~40 MHz)
Start up time	t_str	ms	-	1.0		5.0		t=0 at 90 %Vcc
	_			1.0				10 %Vcc to 90 %Vcc level
Rise time	tr	ns	-	-		8.0	0	CMOS output
Fall time	tf	ns	-	-		8.0	0	90 %Vcc to 10 %Vcc level CMOS output
			45	50		55	5	50 % V _{CC} level CMOS output
Symmetry	SYM	%						GND level (DC-cut)
			40	50		60)	Clipped sine wave (Option)
High output voltage	Vон	V	90 % Vcc	-		-		CMOS output
Low output voltage	Vol	V	-	-		10 %		CMOS output
Output level	Vpp	V	0.8	-		-		Clipped sine wave
			-	-69 -98		-		1 Hz offset 10 Hz offset
Phase Noise 10 MHz			-	-98		-		100 Hz offset
TCXO mode	L(f)	dBc/Hz	-	-144		-		1 kHz offset
	L(I)	ube/Hz	-	-152		-		10 kHz offset
			-	-153		-		100 kHz offset
			-	-154		-		1 MHz offset
			-	-63 (-60		-		1 Hz offset
			-	-92 (-90		-		10 Hz offset
Phase Noise 19.2 MHz	1.(0)		-	-119 (-11 -140 (-13		-		100 Hz offset 1 kHz offset
TCXO mode () is VC-TCXO mode	L(f)	dBc/Hz	-	-153 (-15		-		10 kHz offset
			-	-154 (-15		-		100 kHz offset
			-	-155 (-15		-		1 MHz offset
		dBc/Hz	-	-62 (-62		-		1 Hz offset
			-	-92 (-90		-		10 Hz offset
Phase Noise 20 MHz			-	-119 (-11		-		100 Hz offset
TCXO mode	L(f)		-	-140 (-13		-		1 kHz offset
() is VC-TCXO mode			-	-152 (-15		-		10 kHz offset 100 kHz offset
			-	-154 (-15 -154 (-15		-		1 MHz offset
			-	-62 (-60	,	-		1 Hz offset
	L(f) dBo		-	-93 (-90	/	-		10 Hz offset
Phase Noise 25 MHz TCXO mode () is VC-TCXO mode			-	-118 (-11	/	-		100 Hz offset
		dBc/Hz	-	-139 (-13		-		1 kHz offset
			-	-153 (-15		-		10 kHz offset
			-	-154 (-15	54)	-		100 kHz offset
Phase Noise 40 MHz TCXO mode		dBc/Hz	-	-156 (-15	-	-		1 MHz offset
			-	-59 (-54	/	-		1 Hz offset
			-	-89 (-83		-		10 Hz offset
	1 (1)		-	-114 (-11		-		100 Hz offset
	L(f)		-	-135 (-13		-		1 kHz offset 10 kHz offset
() is VC-TCXO mode			-	-150 (-14 -152 (-15		-		10 kHz offset
			-	-152 (-15		-		1 MHz offset
			-	-100 (-10	,0)	ı -		

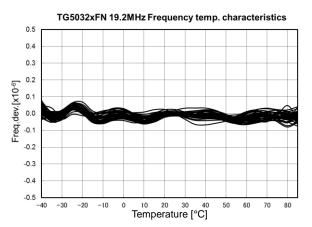
3-2) Frequency control characteristics (V_{CC} = Typ., GND = 0.0 V, V_C = Typ. V, Load = Typ., T_use = +25 °C)

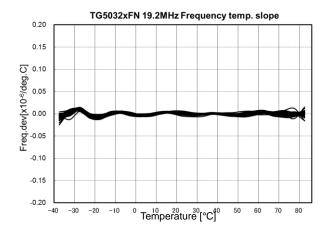
3. Characteristics

3-1) "Frequency / Temperature Characteristics"

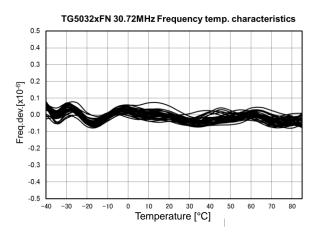
3-1-1) Standard spec : $\pm 0.1 \times 10^{-6}$ Max. (T_use = -40 °C to +85 °C)

19.2 MHz [N = 40 pcs]





30.72 MHz [N = 40 pcs]



0.15 0.10 0.05

Temperature [°C]

0

0.20

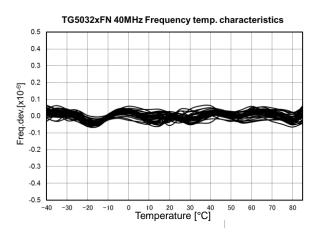
-0.20

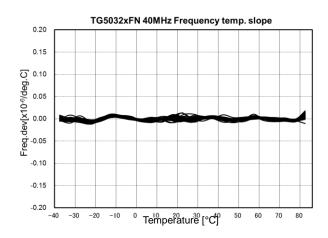
-40

-30 -20 -10

TG5032xFN 30.72MHz Frequency temp. slope

40 MHz [N = 40 pcs]





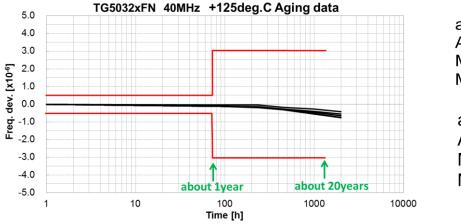
70

80

50 60

3-2) Frequency Aging (40 MHz) [N = 5 pcs]

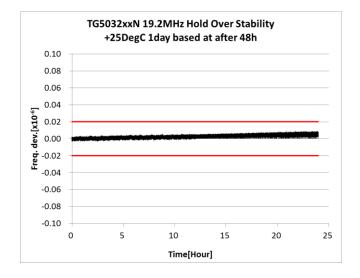
* Aging is estimated from environmental reliability tests and the expected amount of frequency variation over time. It is not intended as a guarantee of performance over the product-life cycle.



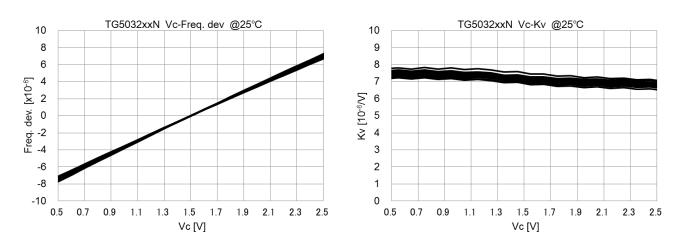
about 1year Ave. : -0.10 x 10⁻⁶ Max. : -0.05 x 10⁻⁶ Min. : -0.12 x 10⁻⁶

about 20years Ave. : -0.54 x 10⁻⁶ Max. : -0.35 x 10⁻⁶ Min. : -0.66 x 10⁻⁶

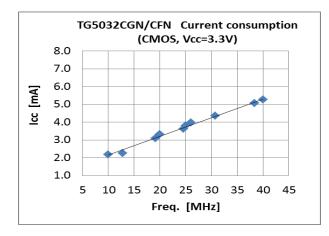
3-3) Holdover Stability (19.2 MHz) [N = 40 pcs]



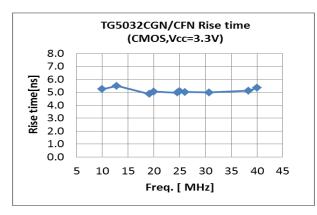




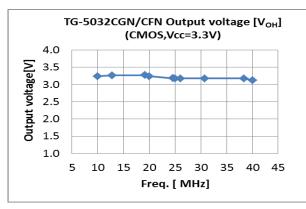
3-5) Current Consumption



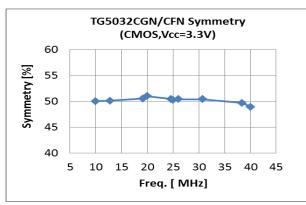
3-6) Rise time / Fall time (at CMOS output)

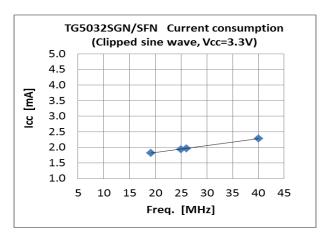


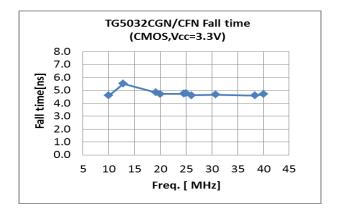
3-7) Output voltage [Voн, VoL] (at CMOS output)

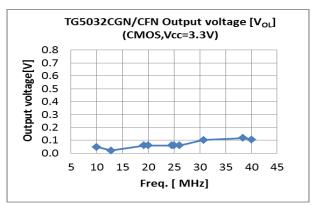


3-8) Symmetry (at CMOS output)

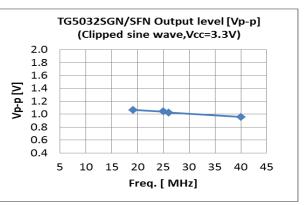






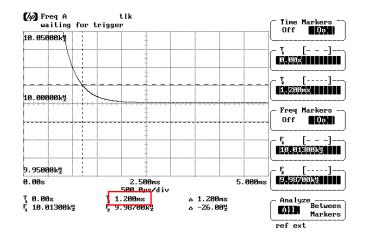


2-9) Output level [VPP] (at Clipped sine wave)

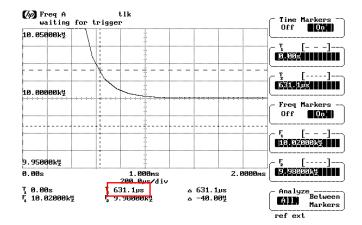


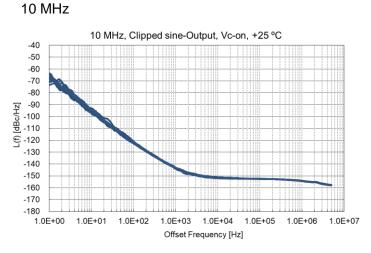
3-10) Start up time (19.2 MHz, 40 MHz)

19.2 MHz



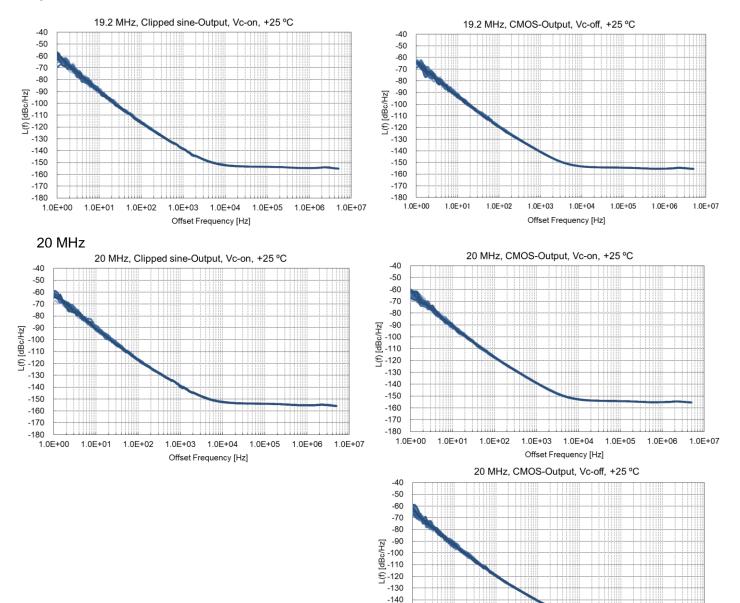
40 MHz





3-11) Phase noise (10 MHz, 19.2 MHz, 20 MHz) [N = 25 pcs]

19.2 MHz



1.0E+05

1.0E+06

1.0E+07

-150 -160 -170 -180 1.0E+00

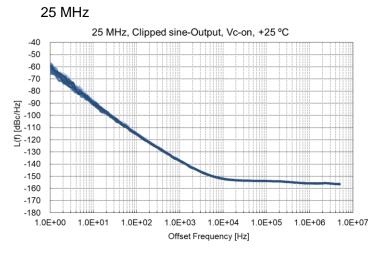
1.0E+01

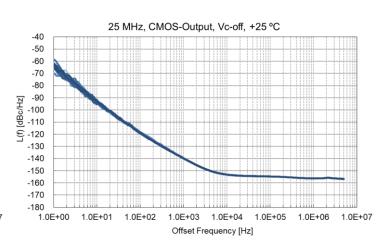
1.0E+02

1.0E+03 1.0E+04

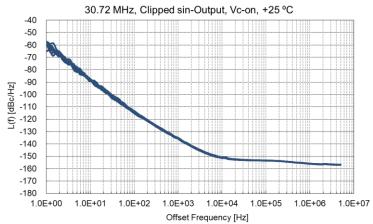
Offset Frequency [Hz]

3-11) Phase noise (25 MHz, 30.72 MHz, 40 MHz) [n = 25 pcs]

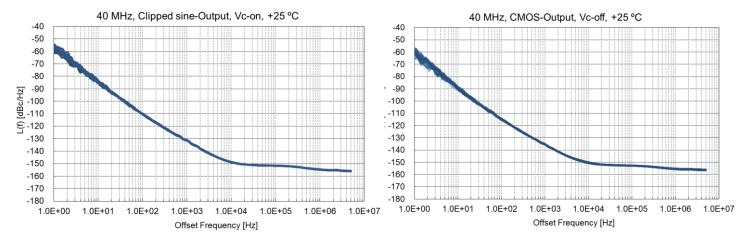


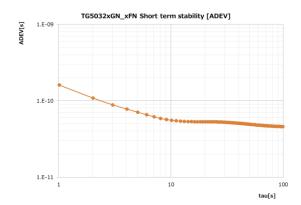


30.72 MHz



40 MHz





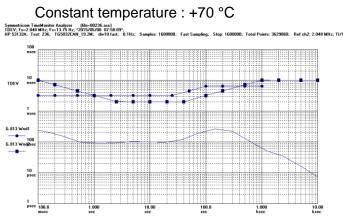
3-12) Short term stability [ADEV] (19.2 MHz) TCXO mode

3-13) TDEV (19.2 MHz, Loop BW = 0.1 Hz)

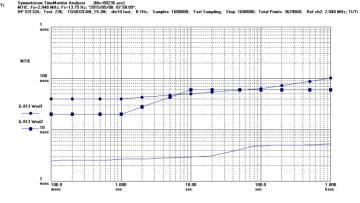
Constant temperature : +25 °C Symmetricom TimeMonitor Analyzer [file=00190.asc] TDEV; Fo=2.048 MHz; Fs=13.20 Hz; *2015/04/24 08:10:40*; HP 53132A; Test: 190; TG5032CAN_19.2M; div10 fast; 0 100 nsec 10 nse TDEV 1 nse 6.813 Wnd1 100 G.813 Wnd2sec 10 psec 1 psec 100.0 10.0 1.000 3-14) MTIE (19.2 MHz, Loop BW = 0.1 Hz) Constant temperature : +25 °C Symmetricom TimeMonitor Analyzer (file=00190.asc) MTIE; Fo=2.048 MHz; Fs=13.20 Hz; *2015/04/24 08:10: HP 53132A; Test: 190; TG5032CAN 19.2M: div10 fas 1 use MTIE 100 nsec

G.813 Wnd1 G.813 Wnd2 1 nsec 100.0 msec 100

Compliant with G.813 option1 and 2

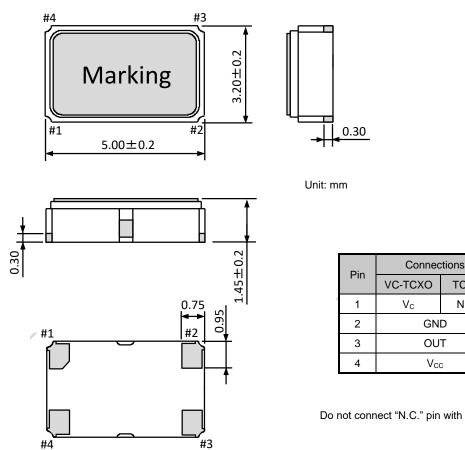


Constant temperature : +70 °C



4. Outline

4-1) Outline dimensions and Pin information



TG5032CFN / SFN

Do not connect "N.C." pin with any other pins (also mutually)

тсхо N.C.

GND

OUT

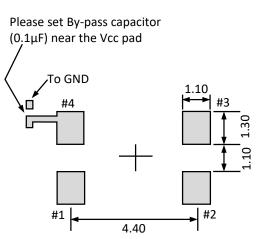
 V_{CC}

4-2) Soldering pattern

Example of patterning design indicated as follows. In an actual design, please consider mounting density, the reliability of soldering, etc. and check whether performance is optimal.

Soldering pattern of TG5032CFN / SFN

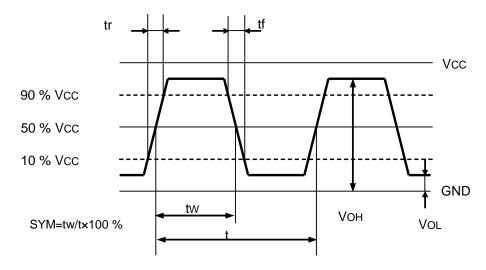
unit : mm



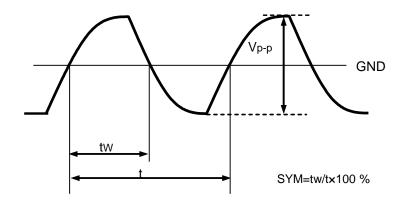
To maintain stable operation, provide a 0.1uF by-pass capacitor at a location as near as possible to the power source terminal of the crystal product (between Vcc - GND).

5. Timing chart

5-1) Output waveform (CMOS output)



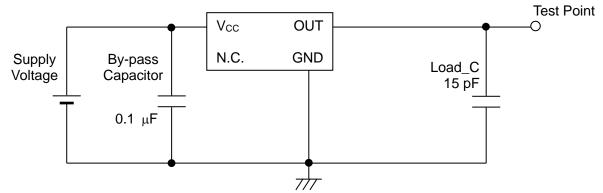
5-2) Output waveform (Clipped sine wave output)



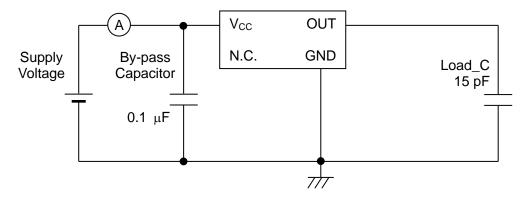
6. Test circuit

6-1) CMOS output for TCXO

1) Output Load : 15 pF



2) Current consumption



3) Conditions

1. Oscilloscope:	Impedance	Min. 1 MΩ
	Input capacitance	Max. 10 pF
	Band width	Min. 300 MHz

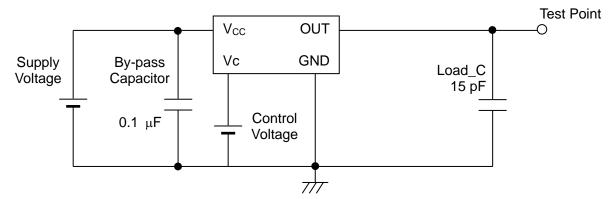
- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 $\,\mu\text{F})$ is placed between Vcc and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- 5. Power Supply

Impedance of power supply should be as low as possible.

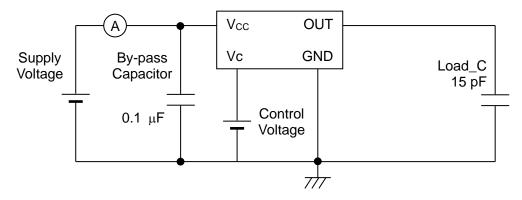
6. GND pin should be connected to low impedance GND.

6-2) CMOS output for VC-TCXO

1) Output Load : 15 pF



2) Current consumption



3) Conditions

1. Oscilloscope:	Impedance	Min. 1 MΩ
	Input capacitance	Max. 10 pF
	Band width	Min. 300 MHz

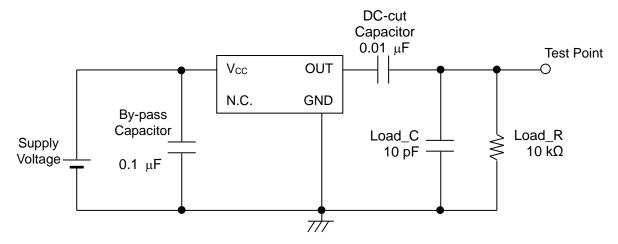
- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 μ F) is placed between V_{CC} and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- 5. Power Supply

Impedance of power supply should be as low as possible.

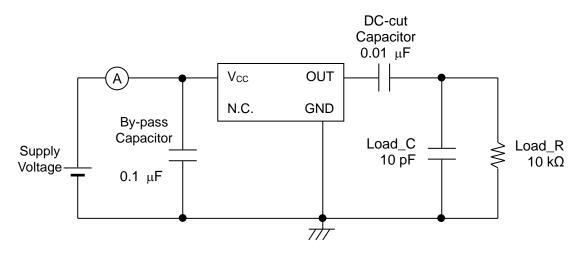
6. GND pin should be connected to low impedance GND.

6-3) Clipped sine wave output for TCXO

1) Output Load : 10 kΩ // 10 pF



2) Current consumption



3) Conditions

1. Oscilloscope:	Impedance	Min. 1 MΩ
	Input capacitance	Max. 10 pF
	Band width	Min. 300 MHz

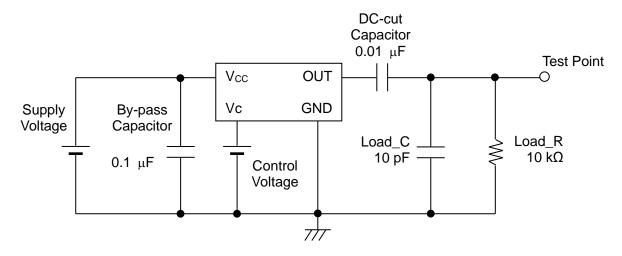
- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 $\,\mu\text{F})$ is placed between Vcc and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- 5. Power Supply

Impedance of power supply should be as low as possible.

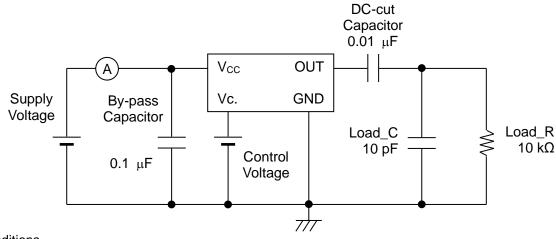
6. GND pin should be connected to low impedance GND.

6-4) Clipped sine wave output for VC-TCXO

1) Output Load : 10 k Ω // 10 pF



2) Current consumption



3) Conditions

 1. Oscilloscope:
 Impedance
 Min. 1 MΩ

 Input capacitance
 Max. 10 pF

 Band width
 Min. 300 MHz

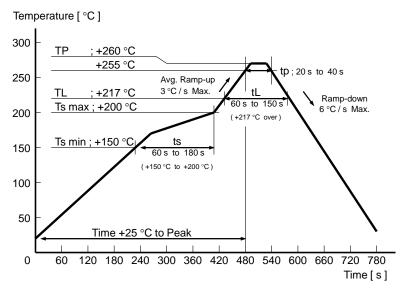
- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 $\,\mu\text{F})$ is placed between Vcc and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.

5. Power Supply

Impedance of power supply should be as low as possible.

6. GND pin should be connected to low impedance GND.

7. Reflow profile (follow to IPC / JEDEC J-STD-020D.1)



8. Packing information

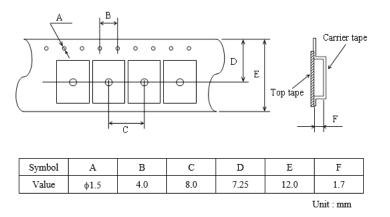
(8-1) Product number last 2 digits code (00) define Quantity. 1 000 pcs/Reel.

TG5032CFN: X1G005391xxxx00 (Please contact Epson for details of number xxxx) TG5032SFN: X1G005401xxxx00

(8-2) Taping specification Subject to EIA-481 IEC-60286 JIS C0806

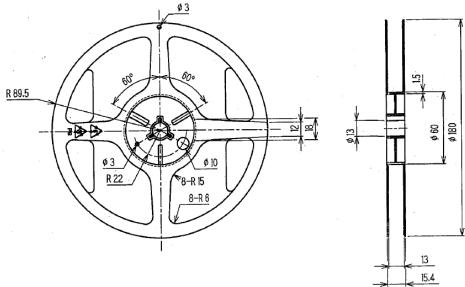
(1) Tape dimensions

Material of the Carrier Tape: PS conduct / Material of the Top Tape: PET



(2) Reel dimensions

Material of the reel: Conductive polystyrene



9. Moisture Sensitivity Level, Electro-Static Discharge

(9-1) Moisture Sensitivity Level (MSL)

Parameter	Specifications	Conditions
MSL	LEVEL1	JEDEC J-STD-020D

(9-2) Electro-Static Discharge (ESD)

Parameter	Specifications	Conditions
Human Body Model (HBM)	2 000 V Min	EIAJ ED-4701-1 C111A, 100 pF, 1.5 kΩ, 3 times
Machine Model (MM)	200 V Min	EIAJ ED-4701-1 C111, 200 pF, 0 Ω, 1 time

10. Handling precautions

Prior to using this product, please carefully read the section entitled "Precautions" on our Web site (<u>https://www5.epsondevice.com/en/information/#precaution</u>) for instructions on how to handle and use the product properly to ensure optimal performance of the product in your equipment. Before using the product under any conditions other than those specified therein,

please consult with us to verify and confirm that the performance of the product will not be negatively affected by use under such conditions.

In addition to the foregoing precautions, in order to avoid the deteriorating performance of the product, we strongly recommend that you DO NOT use the product under ANY of the following conditions:

- (1) Do not expose this product to excessive mechanical shock or vibration.
- (2) This product can be damaged by mechanical shock during the soldering process depending on the equipment used, process conditions, and any impact forces experienced. Always follow appropriate procedures, particularly when changing the assembly process in anyway and be sure to follow applicable process qualification standards before starting production.
- (3) These devices are sensitive to ESD, please use appropriate precautions during handling, assembly, test, shipment, and installation.
- (4) This product contains semiconductor content that should not be exposed to electromagnetic waves.
- (5) The use of ultrasonic technology for cleaning, bonding, etc. can damage the Xtal unit inside this product. Please carefully check for this consideration before using ultrasonic equipment for volume production with this product.
- (6) Noise and ripple on the power supply may have undesirable affects on operation and cause degradation of phase noise characteristics. Evaluate the operation of this device with appropriate power supplies carefully before use.
- (7) When applying power, ensure that the supply voltage increases monotonically for proper operation. On power down, do not reapply power until the supplies, bypass capacitors, and any bulk capacitors are completely discharged since that may cause the unit to malfunction.
- (8) Aging specifications are estimated from environmental reliability tests and expected frequency variation over time. They do not provide a guarantee of aging over the product lifecycle.
- (9) The metal cap on top of the device is directly connected to the GND terminal (pin #2). Take necessary precautions to prevent any conductor not at ground potential from contacting the cap as that could cause a short circuit to GND.
- (10)Do not route any signal lines, supply voltage lines, or GND lines underneath the area where the oscillators are mounted including any internal layers and on the opposite side of the PCB. To avoid any issues due to interference of other signal lines, please take care not to place signal lines
 - near the product as this may have an adverse affect on the performance of the product.
- (11)A bypass capacitor of the recommended value(s) must be connected between the V_{CC} and GND terminals of the product. Whenever possible, mount the capacitor(s) on the same side of the PCB and as close to the product as possible to keep the routing traces short.
- (12)Power supply connections to V_{CC} and GND pins should be routed as thick as possible while keeping the high frequency impedance low in order to get the best performance.
- (13) The use of a filter or similar element in series with the power supply connections to protect from electromagnetic radiation noise may increase the high frequency impedance of the power supply line and may cause the oscillator to not operate properly. Please verify the design to ensure sufficient operational margin prior to use.
- (14) Keep PCB routing from the output terminal(s) to the load as short as possible for best performance.
- (15) Do not short the output to GND as that will damage the product. Always use with an appropriate load resistor connected.
- (16) Product failures during the warranty period only apply when the product is used according to the recommended operating conditions described in the specifications. Products that have been opened for analysis or damaged will not be covered. It is recommended to store and use in normal temperature and humidity environments described in the specifications to ensure frequency accuracy and prevent moisture condensation. If the product is stored for more than one year, please confirm the pin solderability prior to use.
- (17) If the oscillation circuit is exposed to condensation, the frequency may change or oscillation may stop. Do not use in any conditions where condensation occurs.
- (18) Do not store or use the product in an environment where it can be exposed to chemical substances that are corrosive to metal or plastics such as salt water, organic solvents, chemical gasses, etc. Do not use the product when it is exposed to sunlight, dust, corrosive gasses, or other materials for long periods of time.
- (19) When using water-soluble solder flux make sure to completely remove the flux residue after soldering.
 - Pay particular attention when the residues contain active halogens which will negatively affect the product and its performance.